

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ\text{C}$
150V	19m Ω @ $V_{GS} = 10\text{V}$	61A
	22m Ω @ $V_{GS} = 8\text{V}$	40A

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and load switch.

Applications

- Motor Control
- DC-DC Converters
- Power Management

Features

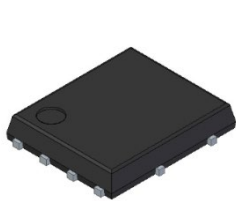
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications (PowerDI®)
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

Mechanical Data

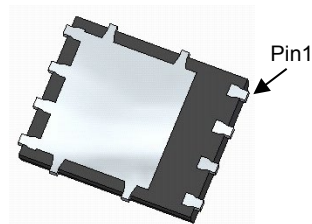
- Case: PowerDI5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish - Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.097 grams (Approximate)

Site 1:

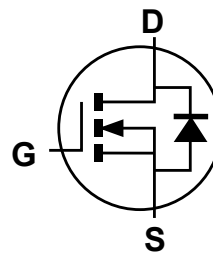
PowerDI5060-8



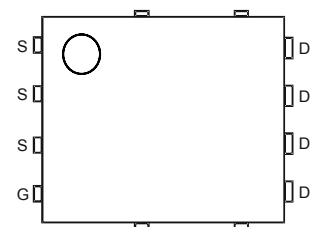
Top View



Bottom View



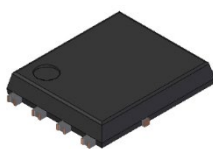
Internal Schematic



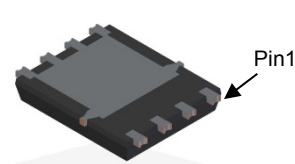
Top View
Pin Configuration

Site 2:

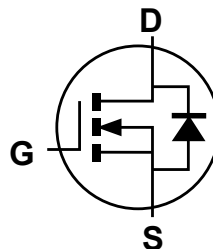
PowerDI5060-8 (SWP) (Type UX)



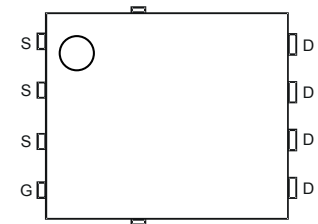
Top View



Bottom View



Internal Schematic



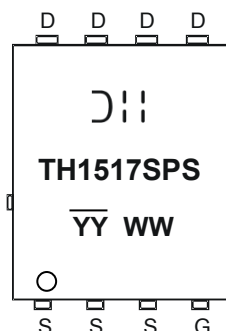
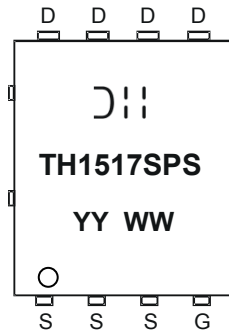
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH15H017SPS-13	PowerDI5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



 Manufacturer's Marking
 TH1517SPS = Product Type Marking Code
 YYWW or YYWW = Date Code Marking
 YY or YY = Last Two Digits of Year (ex: 20 = 2020)
 WW = Week Code (01 to 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	150	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current V _{GS} = 10V (Note 6)	Steady State	T _A = +25°C	I _D	11	A
		T _A = +100°C		7	
Continuous Drain Current V _{GS} = 10V (Note 7)	Steady	T _C = +25°C	I _D	61	A
	State	T _C = +100°C		40	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	250	A
Maximum Continuous Body Diode Forward Current			I _S	61	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	250	A
Avalanche Current (Note 8), L = 3mH			I _{AS}	14.4	A
Avalanche Energy (Note 8), L = 3mH			E _{AS}	311	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	97	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	47	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	107	W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	1.4	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	150	—	—	V	$V_{GS} = 0V, I_D = 10mA$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 120V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	14	19	m Ω	$V_{GS} = 10V, I_D = 20A$
		—	16	22		$V_{GS} = 8V, I_D = 15A$
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	$V_{GS} = 0V, I_S = 20A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	2344	—	pF	$V_{DS} = 75V, V_{GS} = 0V$ $f = 1MHz$
Output Capacitance	C_{oss}	—	213	—		
Reverse Transfer Capacitance	C_{rss}	—	6.9	—		
Gate Resistance	R_g	—	1.8	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	—	34	—	nC	$V_{DD} = 75V, I_D = 20A,$ $V_{GS} = 10V$
Gate-Source Charge	Q_{gs}	—	12	—		
Gate-Drain Charge	Q_{gd}	—	9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	13.2	—	ns	$V_{DD} = 75V, V_{GS} = 10V,$ $I_D = 20A, R_g = 6\Omega$
Turn-On Rise Time	t_R	—	22.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.3	—		
Turn-Off Fall Time	t_F	—	16.1	—		
Reverse Recovery Time	t_{RR}	—	69	—	ns	$I_F = 20A, di/dt = 100A/\mu s$
Reverse Recovery Charge	Q_{RR}	—	196	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

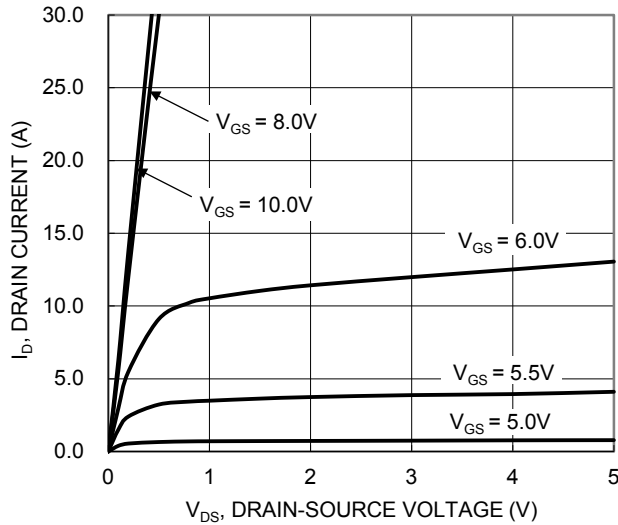


Figure 1. Typical Output Characteristic

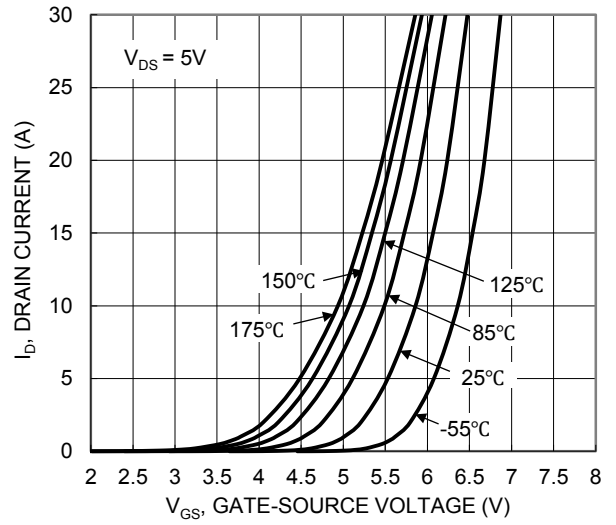


Figure 2. Typical Transfer Characteristic

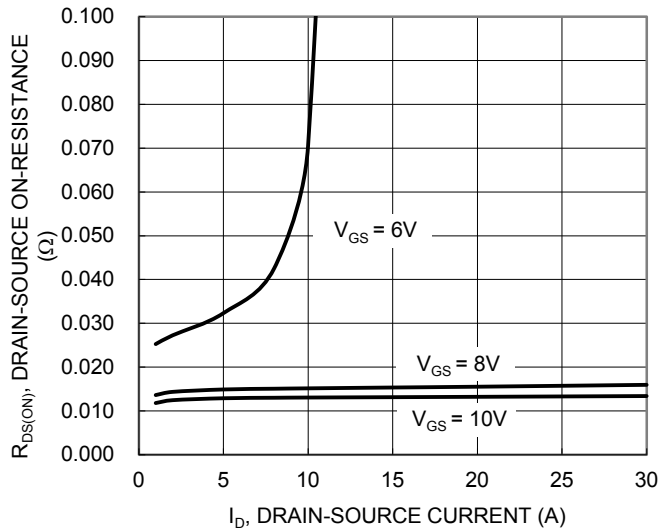


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

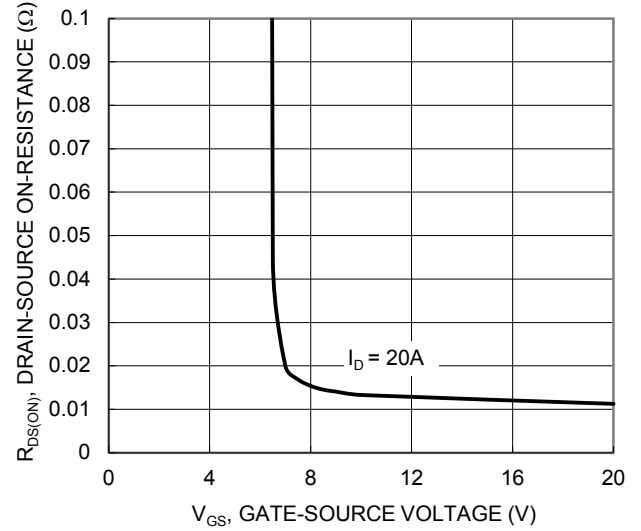


Figure 4. Typical Transfer Characteristic

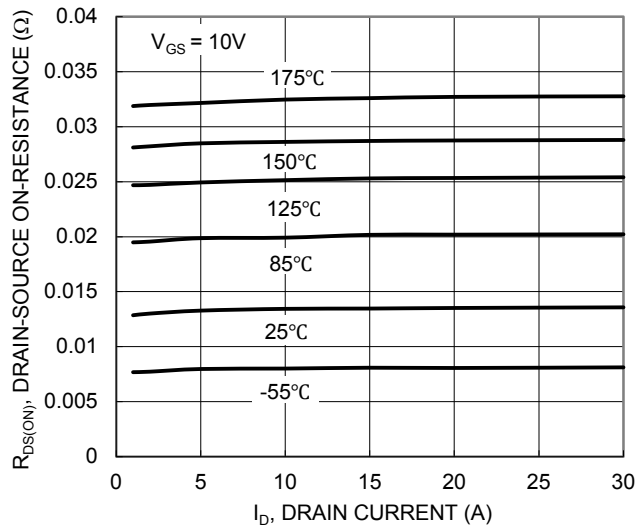


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

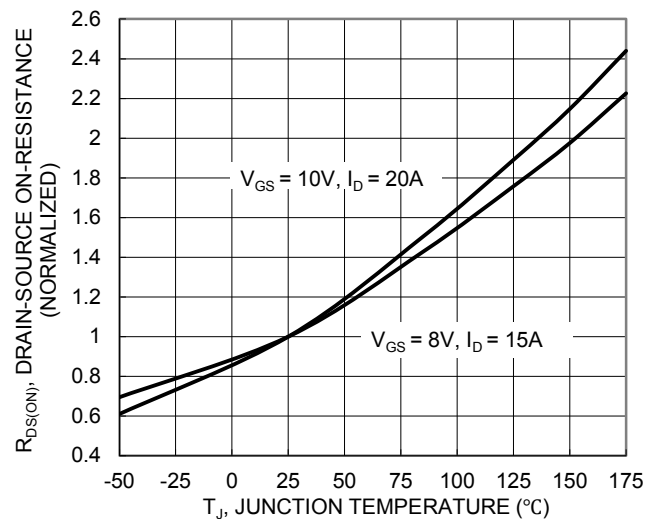


Figure 6. On-Resistance Variation with Temperature

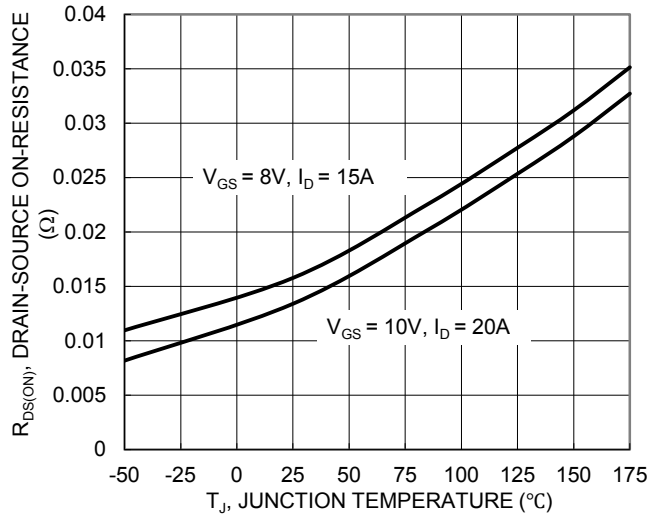


Figure 7. On-Resistance Variation with Temperature

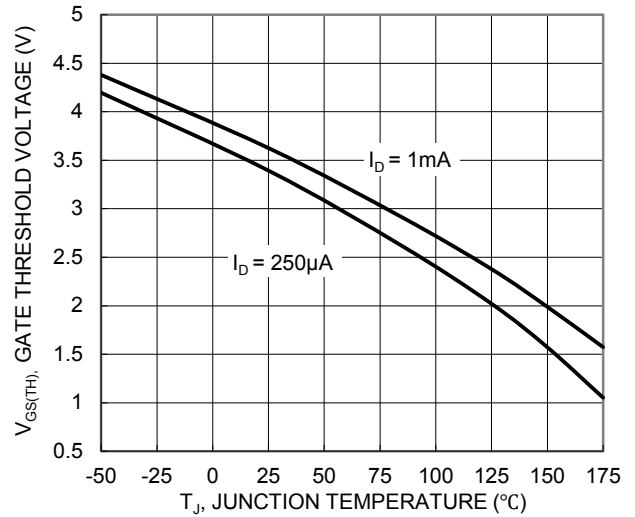


Figure 8. Gate Threshold Variation vs. Junction Temperature

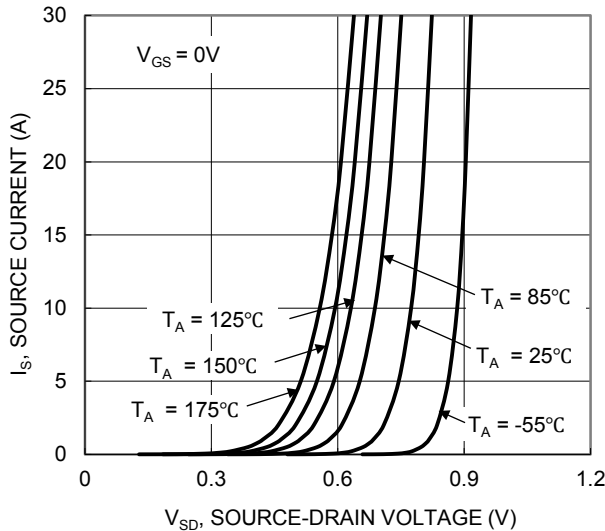


Figure 9. Diode Forward Voltage vs. Current

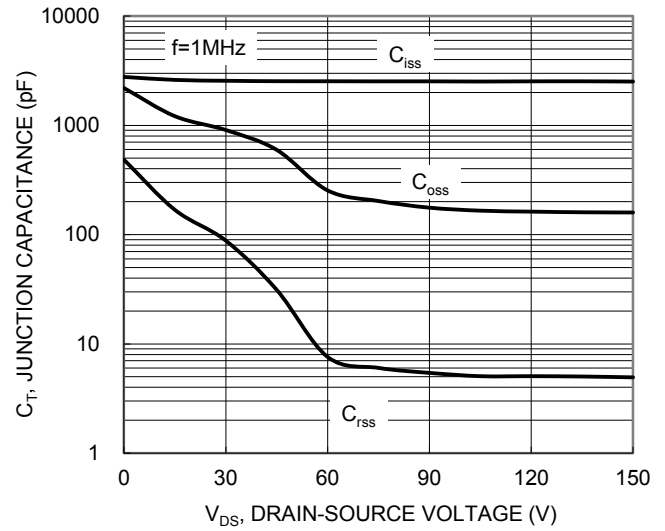


Figure 10. Typical Junction Capacitance

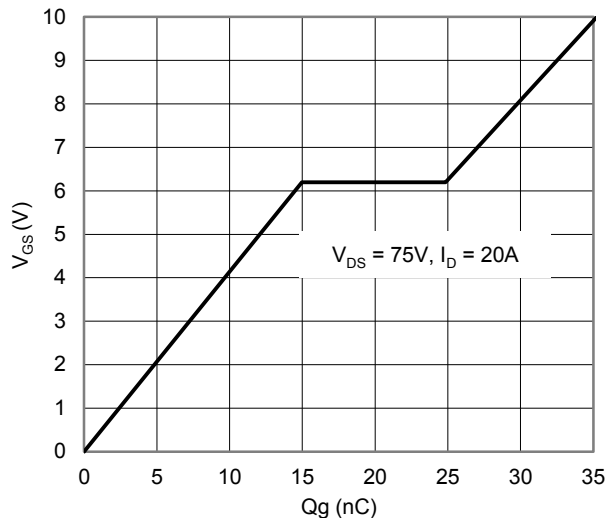


Figure 11. Gate Charge

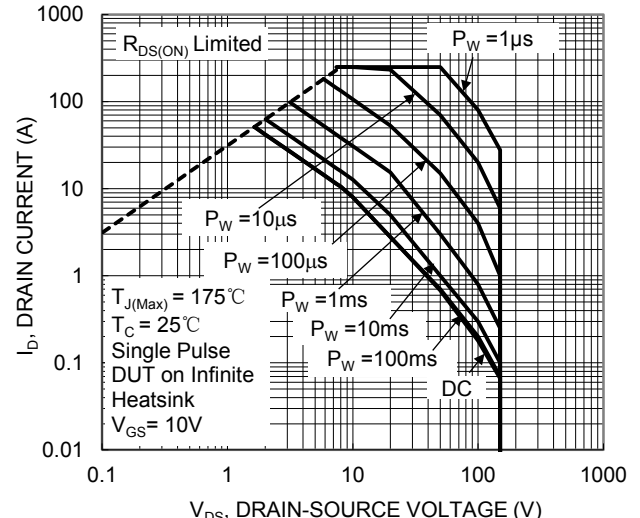


Figure 12. SOA, Safe Operation Area

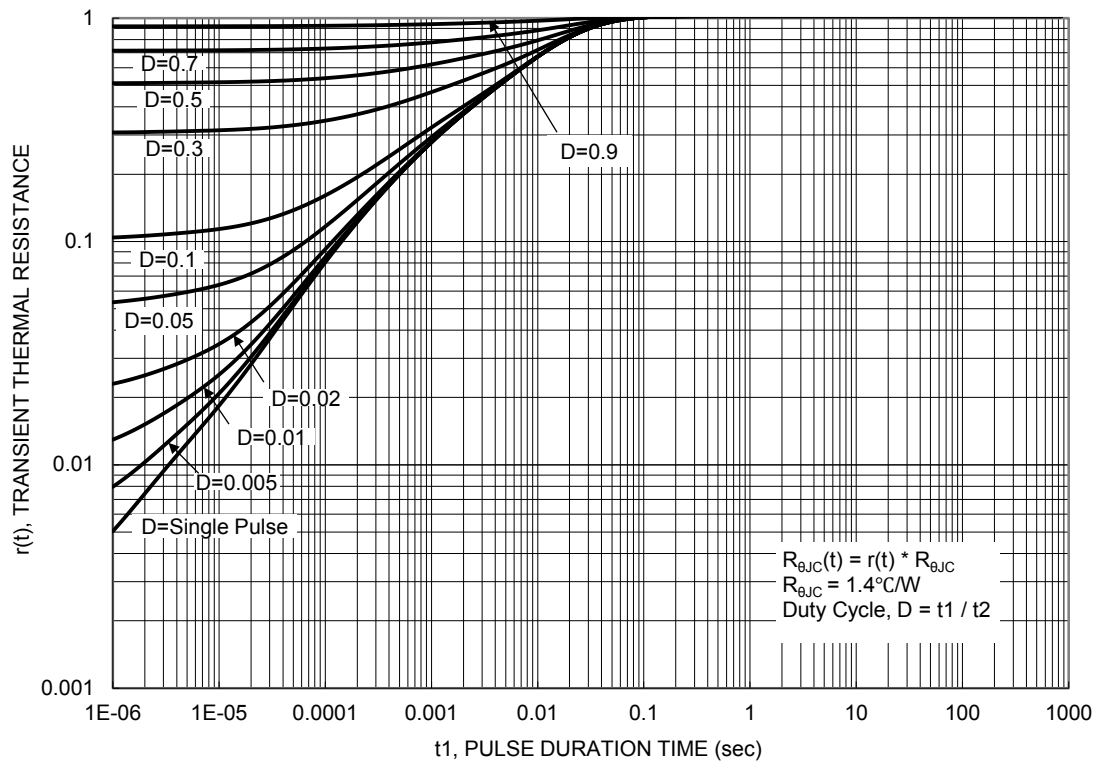


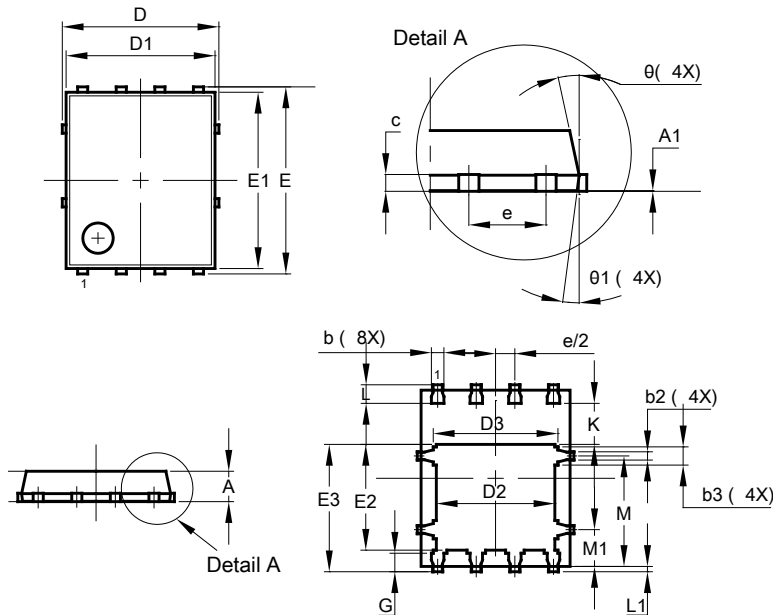
Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

PowerDI5060-8

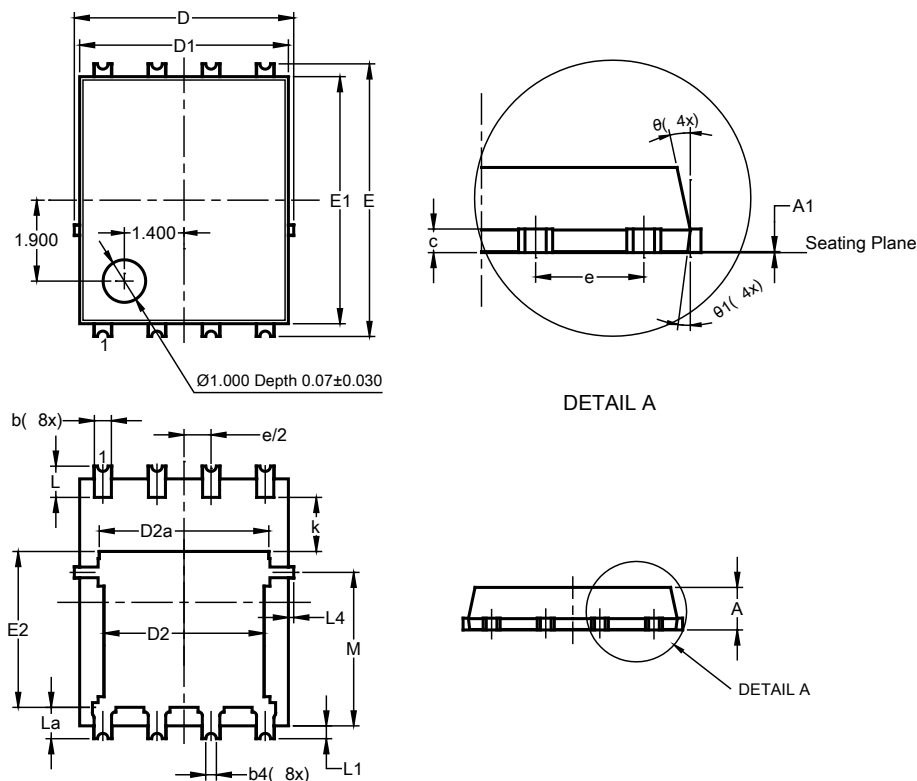


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°

All Dimensions in mm

Site 2:

PowerDI5060-8 (SWP) (Type UX)



PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	—
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	—	—
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°

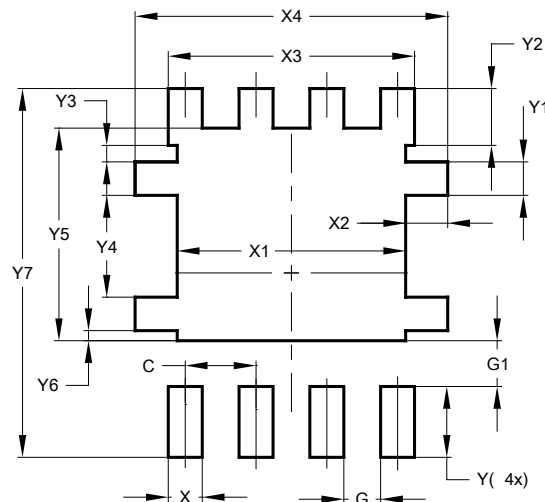
All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

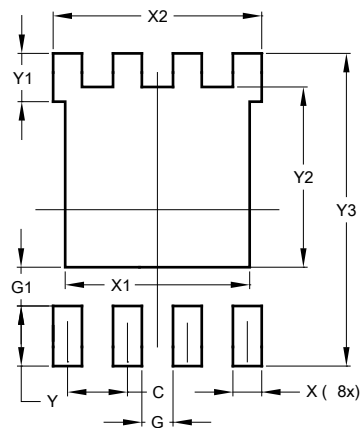
PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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